LISTING OF CLAIMS:

Claim 1 (Original) A method for preparing a film structure of a ferroelectric single crystal, which comprises adhering a ferroelectric single crystal plate to a substrate by a conductive adhesive or metal layer.

Claim 2 (Currently Amended) The method of claim 1, wherein the single crystal plate is polished to a thickness of 1 to 100 μm before ~~and~~ or after the adhesion with the substrate.

Claim 3 (Original) The method of claim 1, wherein the single crystal plate is adhered to the substrate by placing a conductive adhesive between the single crystal plate and the substrate and heat treating the resulting laminate containing the adhesive at a temperature ranging from room temperature to 150 °C for 1 to 24 hours to cure the adhesive.

Claim 4 (Original) The method of claim 3, wherein the conductive adhesive is a gold- or silver- containing epoxy paste, or a Pt-containing adhesive sol.

Claim 5 (Currently Amended) The method of claim 3, ~~which~~ wherein the adhesive is applied using a plate equipped with a pressurizing rod having a round terminal portion made of an elastic rubber.

Claim 6 (Original) The method of claim 1, wherein the single crystal plate is adhered to the substrate by depositing a conductive metal on each surface of the single crystal plate and the substrate, combining the two conductive metal layers, and pressurizing and heat-treating the resulting laminate at a temperature of 100 to 600 °C.

Claim 7 (Original) The method of claim 6, which further comprises inserting a plate of a metal having a melting point lower than that of the conductive metal between the two conductive metal layers prior to the pressurizing and heat-treating step of the laminate.

Claim 8 (Original) The method of claim 1, wherein the ferroelectric single crystal has a dielectric constant of 1,000 or greater as measured in a film form.

Claim 9 (Original) The method of claim 1, wherein the ferroelectric single crystal is $LiNbO_3$, $LiTaO_3$ or a material having the composition of formula (I):

$x(A)y(B)z(C)\text{-}p(P)n(N)$ (I)

wherein,

(A) is $Pb(Mg_{1/3}Nb_{2/3})O_3$ or $Pb(Zn_{1/3}Nb_{2/3})O_3$,

(B) is $PbTiO_3$,

(C) is $LiTaO_3$,

(P) is a metal selected from the group consisting of Pt, Au, Ag, Pd and Rh,

(N) is an oxide of a metal selected from the group consisting of Ni, Co, Fe, Sr, Sc, Ru, Cu and Cd,

x is a number in the range of 0.65 to 0.98,

y is a number in the range of 0.01 to 0.34,

z is a number in the range of 0.01 to 0.1, and

p and n are each independently a number in the range of 0.01 to 5.

Claim 10 (Original) The method of claim 1, wherein the substrate comprises a layer of an oxide material selected from SiO_2, MgO, Al_2O_3 and ZnO, the oxide layer being contacted with the conductive adhesive layer.

Claim 11 (Original) The method of claim 1, which further comprises forming a conductive metal layer on the surface of the single crystal plate opposite to the adhesive layer by a sputtering or an electronic beam evaporation method.

Claim 12 (Currently Amended) A ferroelectric single crystal film structure prepared by a method according to ~~any one of claims 1 to 11~~ claim 1.

Claim 13 (Original) An electric or electronic device comprising the ferroelectric single crystal film structure according to claim 12.